

Silicon Variable Capacitance Diode

- For FM radio tuner with extended frequency band 77MHz to 108MHz
- Designed for application requiring back-to-back diode configuration for optimum signal distortion and detuning
- High tuning ratio at low supply voltage (car radio)
- Monolitic chip (common cathode) for perfect dual diode tracking
- Good C- V linearity
- High figure of merit
- Pb-free (RoHS compliant) package



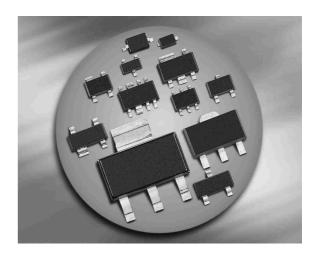
BB844



| Туре | Package | Configuration | L _S (nH) | Marking |
|-------|---------|----------------|---------------------|---------|
| BB844 | SOT23 | common cathode | 1.8 | SNs |

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

| Parameter | Symbol | Value | Unit | |
|-----------------------------|------------------|---------|------|--|
| Diode reverse voltage | V _R | 18 | V | |
| Peak reverse voltage | V _{RM} | 20 | | |
| Forward current | I _F | 50 | mA | |
| Operating temperature range | T _{op} | -55 150 | °C | |
| Storage temperature | T _{stq} | -55 150 | | |





| Parameter | Symbol | Values | | | Unit |
|--|----------------------------------|--------|-------|------|------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Reverse current | I _R | | | | nA |
| V _R = 16 V | | - | - | 20 | |
| <i>V</i> _R = 16 V, <i>T</i> _A = 85 °C | | - | - | 200 | |
| AC Characteristics | | | | | |
| Diode capacitance | CT | | | | pF |
| V _R = 2 V, <i>f</i> = 1 MHz | | 42.5 | 43.75 | 45 | |
| V _R = 4 V, <i>f</i> = 1 MHz | | 25 | 27 | 29 | |
| V _R = 8 V, <i>f</i> = 1 MHz | | 10 | 11.5 | 13 | |
| Capacitance ratio | C _{T2} /C _{T8} | 3.2 | 3.8 | - | |
| V _R = 2 V, V _R = 8 V, <i>f</i> = 1 MHz | | | | | |
| Capacitance matching ¹⁾ | ΔC _T /C _T | - | - | 1.5 | % |
| $V_{\rm R}$ = 2V to 8V , f = 1 MHz | | | | | |
| Series resistance | r _S | - | 0.28 | - | Ω |
| V _R = 2 V, <i>f</i> = 100 MHz | | | | | |

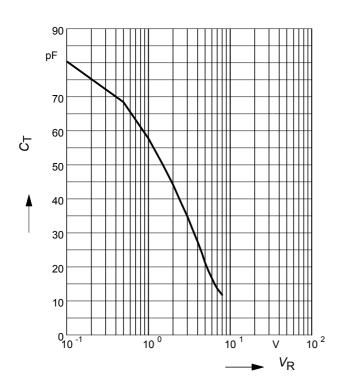
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

¹For details please refer to Application Note 047.

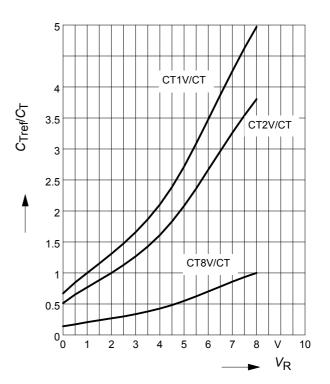


Diode capacitance $C_{T} = f(V_{R})$

f = 1 MHz



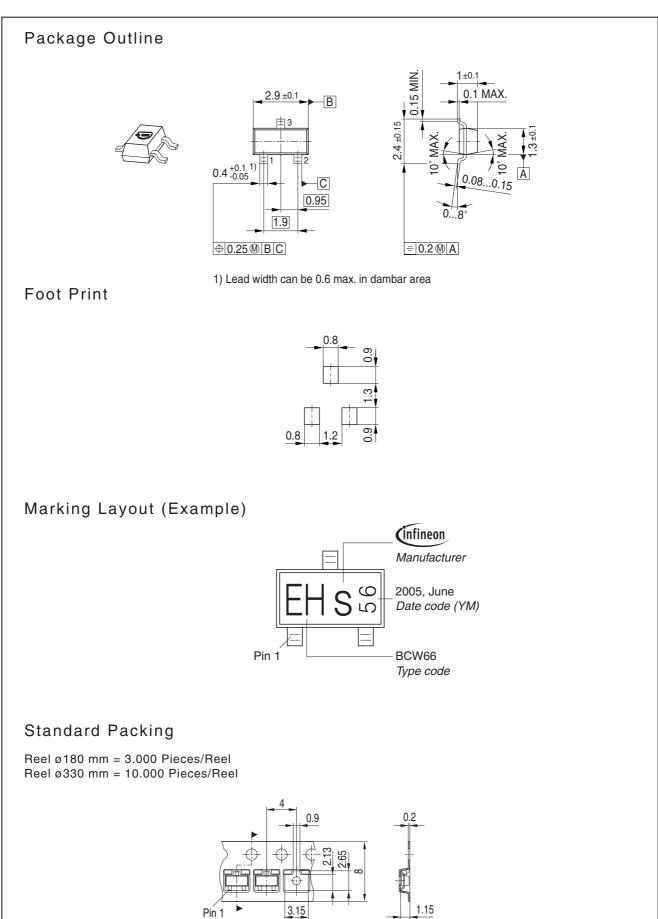
Capacitance ratio $C_{\text{Tref}}/C_{\text{T}} = f(V_{\text{R}})$ f = 1 MHz



Temperature coefficient of the diode capacitance $T_{CC} = f(V_R)$









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